

2N1870AS-2N1874AS

SILICON CONTROLLED RECTIFIERS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Ratings	Symbol	2N1870AS	2N1871AS	2N1872AS	2N1873AS	2N1874AS	Unit
Repetitive peak off state voltage	V _{DRM}	30	60	100	150	200	V
Repetitive peak reverse voltage	V _{RRM}	30	60	100	150	200	V
DC on state current							
100°C ambient	Ι _Τ	250					mA
100°C case				1.25			Α
Repetitive peak on state current	I _{TRM}	Up to 30					
Peak one cycle surge (non-repetitive) on state current	I _{TSM}			15			А
Peak gate current	I _{GM}			250			mA
Average gate current	I _{G(AV)}	25					mA
Reverse gate voltage	V_{GR}	5					V
Thermal resistance, junction to case	R _{OJC}	20					°C/W
Operating and storage temperature range	T _J , T _{stg}	-65 to 150					°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

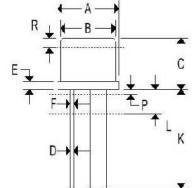
Test	Symbol	Min.	Тур.	Max.	Units	Test Conditions
25°C tests						
Off-state current	I _{DRM}	-	0.5	10	μА	R _{GK} = 1K, V _{DRM} = +rating
Reverse current	I _{RRM}	-	0.5	10	μА	R _{GK} = 1K, V _{RRM} = - rating
Gate trigger voltage	V_{GT}	0.4	0.55	0.8	V	R _{GS} = 100ohms, V _D = 5V
Gate trigger current	l _{GT}	-	30	200	μА	$R_{GS} > 10K \text{ ohms, } V_D = 5V$
On-state voltage	V _{TM}	-	1.8	2.5	V	I _{TM} = 2A (pulse test)
Off-state voltage – critical rate of rise	dv₀/dt	100	-	-	V/µs	Specified test circuit
Reverse gate current	I _{GR}	-	0.5	10	μА	V _{GRM} = 5V, anode open
Holding current	lн	0.3	-	5.0	mA	$I_G = -150\mu A$, $V_D = 5V$
125°C tests						
High temperature off state current	I _{DRM}	-	15	100	μА	R _{GK} = 1K, V _{DRM} = + rating
High temperature reverse current	I _{RRM}	-	15	100	μА	R _{GK} = 1K, V _{RRM} = - rating
High temperature gate non-trigger voltage	V_{GD}	0.2	-	-	V	$R_{GS} = 100 \text{ ohms}, V_D = 5V$
High temperature holding current	I _H	0.2	-	-	mA	$I_G = -150 \mu A, V_D = 5V$
-65 °C tests					•	
Low temperature gate trigger voltage	V_{GT}	-	-	1.0	V	R _{GK} = 100 ohms, V _D = 5V
Low temperature gate trigger current	l _{GT}	-	-	500	μА	$R_{GK} > 10K \text{ ohms, } V_D = 5V$
Low temperature holding current	I _H	-	-	15	mA	$I_G = -150 \mu A$, $V_D = 5V$

Voltage ratings apply over the full operating temperature range provided the gate is connected to the cathode through a resistor, 1K or smaller, or other adequate gate bias is used.



MECHANICAL CHARACTERISTICS

Case:	TO-39
Marking:	Alpha numberic
Pin out:	See below



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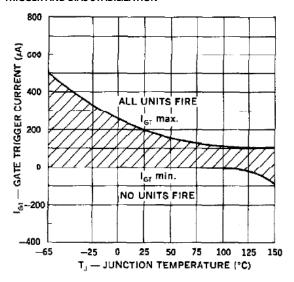
		TO	-39		
	Inc	hes	Millimeters		
	Min	Max	Min	Max	
A	0.335	0.370	8.510	9.390	
В	0.305	0.335	7,750	8.500	
C	0.240	0.260	6.100	6.600	
D	0.016	0.021	0.410	0.530	
Е	0.009	0.041	0.230	1.040	
F	0.016	0.019	0.410	0.480	
G	0.200 BSC		5.080 BSC		
Н	0.028	0.034	0.720	0.860	
J	0.029	0.045	0.740	1.140	
K	0.500	0.750	12.700	19.050	
L	0.250		6.350	- 3	
M	45°C BSC		45°C BSC		
Р	10235	0.050	151	1.270	
R	0.100	1921	2.540	1121	



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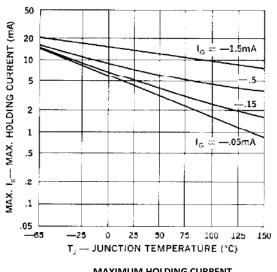
SILICON CONTROLLED RECTIFIERS

TRIGGER AND BIAS STABILIZATION

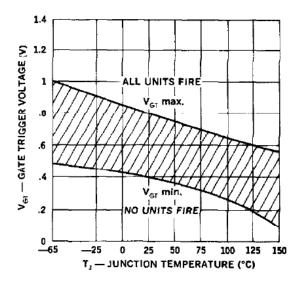


GATE TRIGGER CURRENT

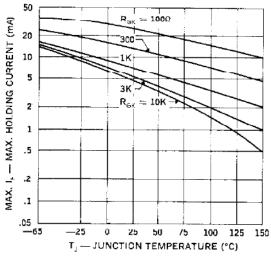
HOLDING CURRENT



MAXIMUM HOLDING CURRENT (CURRENT BIAS)



GATE TRIGGER VOLTAGE



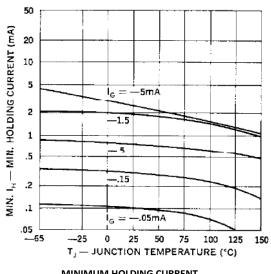
MAXIMUM HOLDING CURRENT (RESISTOR BIAS)



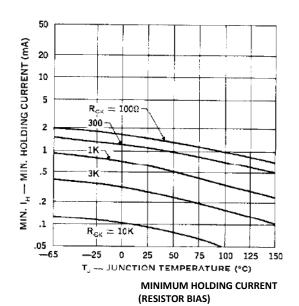
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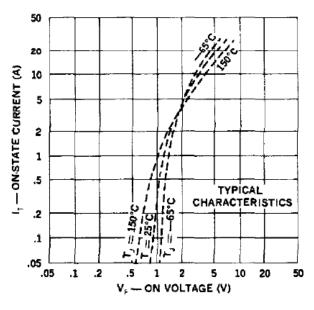
HOLDING CURRENT



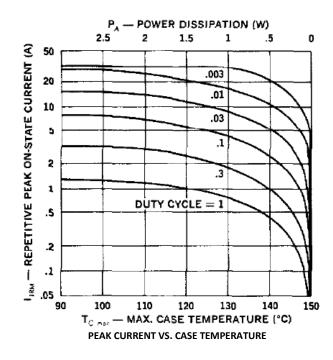
MINIMUM HOLDING CURRENT
(CURRENT BIAS)



CURRENT RATINGS - THERMAL DESIGN



ON-STATE CURRENT VS VOLTAGE

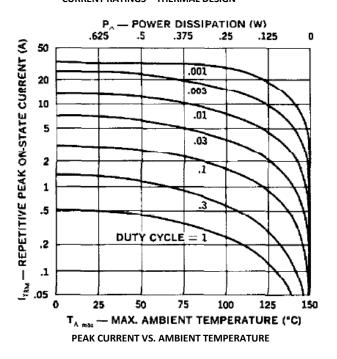




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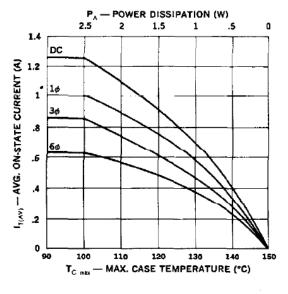
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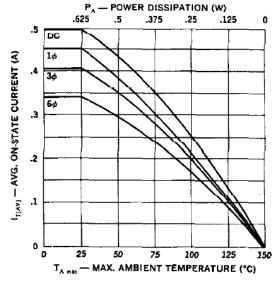
CURRENT RATINGS - THERMAL DESIGN



50 (BEFORE SURGE = 0 20 - PEAK SURGE CURRENT (A) 10 5 SOLID LINE: RATED T_C = 100°C BLOCKING VOLTAGE MAY BE APPLIED IMMEDIATELY AFTER SURGE .5 DASH LINE: BLOCKING VOLTAGE MAY NOT BE SUSTAINED FOR 0.1 SECONDS .2 AFTER SURGE .1 .05 10-5 10-4 10-3 10-2 10-1 1 10 102 103 SURGE DURATION (s)

SURGE CURRENT VS. TIME





AVERAGE CURRENT VS. AMBIENT TEMPERATURE